

isc Silicon NPN Power Transistor

2SC3997

DESCRIPTION

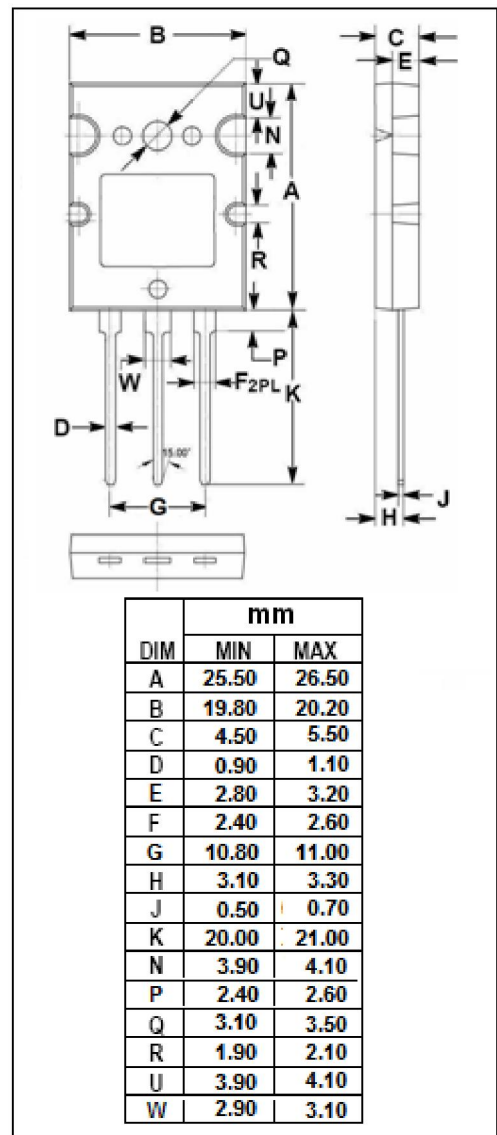
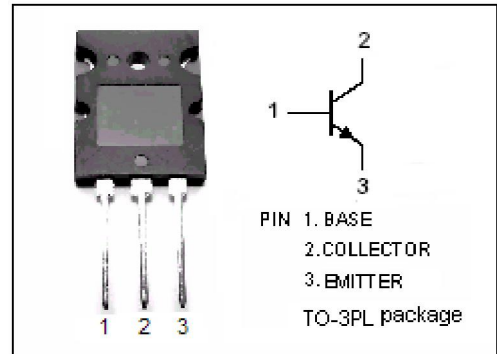
- High Switching Speed
- High Breakdown Voltage-
: $V_{(BR)CBO} = 1500V(\text{Min})$

APPLICATIONS

- Designed for horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	20	A
I_{CM}	Collector Current-Pulse	40	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	250	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SC3997****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = 100\text{mA}; I_B = 0$	800			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 16\text{A}; I_B = 4\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 16\text{A}; I_B = 4\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 800\text{V}; I_E = 0$			10	μA
I_{CES}	Collector Cutoff Current	$V_{CE} = 1500\text{V}; R_{BE} = 0$			1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 4\text{V}; I_C = 0$			1.0	mA
h_{FE-1}	DC Current Gain	$I_C = 1\text{A}; V_{CE} = 5\text{V}$	8			
h_{FE-2}	DC Current Gain	$I_C = 16\text{A}; V_{CE} = 5\text{V}$	4		8	
t_{stg}	Storage Time	$I_C = 12\text{A}, I_{B1} = 2.4\text{A}; I_{B2} = -4.8\text{A}$			3.0	μs
t_f	Fall Time				0.2	μs